

ABSTRACT

An opening is formed in the center of a base 1 on which an input/output electrode pattern 3 is formed. Meanwhile, a plurality of bumps 4 are formed on two opposing sides of an active element surface of the semiconductor integrated circuit 2 so as to mount the semiconductor integrated circuit 2 in the center of the opening.

The semiconductor integrated circuit 2 is connected to the electrode pattern 3 on the base 1 through the plurality of bumps 4 by ultrasonic bonding means. In this way, a small and thin piezoelectric device which has superior bonding characteristics of the semiconductor integrated circuit and the base, which are subjected to flip-chip bonding, and which endures mechanical shock, thermal stress, etc., can be obtained at reduced cost. A method for manufacturing the same is also provided.